ESD Protection Diode

Low Capacitance ESD Protection for High Speed Data

The SZ/NUP2115L has been designed to protect the FlexRay transceiver from ESD and other harmful transient voltage events. This device provides bidirectional protection for each data line with a single compact SOT-23 package, giving the system designer a low cost option for improving system reliability and meeting stringent EMI requirements.

Features

- 200 W Peak Power Dissipation per Line (8/20 µs Waveform)
- Diode Capacitance Matching
- Low Reverse Leakage Current (< 100 nA)
- Low Capacitance High-Speed FlexRay Data Rates
- IEC Compatibility: IEC 61000-4-2 (ESD): Level 4
 - IEC 61000-4-4 (EFT): 50 A 5/50 ns
 - IEC 61000-4-5 (Lighting) 3.0 A (8/20 μs)
- ISO 7637–1, Nonrepetitive EMI Surge Pulse 2, 8.0 A (1/50 μs)
- ISO 7637–3, Repetitive Electrical Fast Transient (EFT) EMI Surge Pulses, 50 A (5/50 ns)
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Applications

- Automotive Networks
 - FlexRay Bus



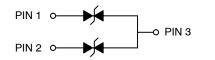
ON Semiconductor®

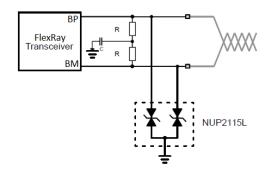
www.onsemi.com

SOT-23 DUAL BIDIRECTIONAL VOLTAGE SUPPRESSOR 200 W PEAK POWER



SOT-23 CASE 318 STYLE 27





MARKING DIAGRAM



25W = Device Code
M = Date Code
Device Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS (T_J = 25°C, unless otherwise specified)

Symbol	Rating	Value	Unit
PPK	Peak Power Dissipation, 8 x 20 μs Double Exponential Waveform (Note 1)	200	W
T _J	Operating Junction Temperature Range	-55 to 150	°C
TJ	Storage Temperature Range	-55 to 150	°C
TL	Lead Solder Temperature (10 s)	260	°C
ESD	Human Body Model (HBM) Machine Model (MM) IEC 61000-4-2 Specification (Contact)	8.0 400 30	kV V kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _{RWM}	Reverse Working Voltage	(Note 2)	24	-	-	V
V _{BR}	Breakdown Voltage	I _T = 1 mA (Note 3)	26.2	-	32	V
I _R	Reverse Leakage Current	V _{RWM} = 24 V	-	15	100	nA
V _C	Clamping Voltage	I _{PP} = 1 A (8/20 μs Waveform) (Note 4)	-	33.4	36.6	V
V _C	Clamping Voltage	I _{PP} = 3 A (8/20 μs Waveform) (Note 4)	-	44	50	V
I _{PP}	Maximum Peak Pulse Current	8/20 μs Waveform (Note 4)	-	-	3.0	Α
CJ	Capacitance	V _R = 0 V, f = 1 MHz (Line to GND)	-	-	10	pF
ΔC	Diode Capacitance Matching	V _R = 0 V, 5 MHz (Note 5)	-	0.1	2	%

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Surge protection devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
- 3. V_{BR} is measured at pulse test current I_T.
- 4. Pulse waveform per Figure 1.
- 5. ΔC is the percentage difference between C_J of lines 1 and 2 measured according to the test conditions given in the electrical characteristics table.

ORDERING INFORMATION

Device	Package	Shipping [†]
NUP2115LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZNUP2115LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NUP2115LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZNUP2115LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} Non-repetitive current pulse per Figure 1.

TYPICAL PERFORMANCE CURVES

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

€

3.5

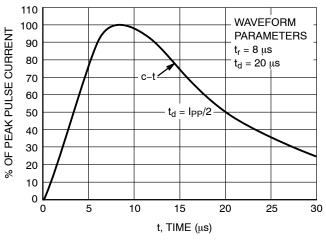
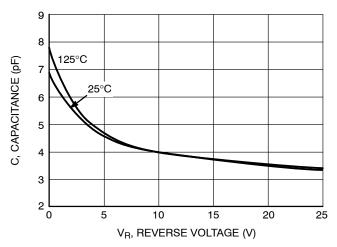


Figure 1. Pulse Waveform, 8 \times 20 μ s

Figure 2. Clamping Voltage vs Peak Pulse Current



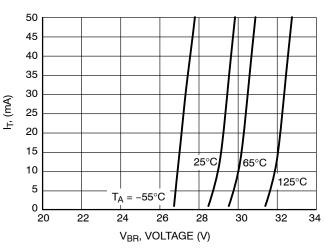
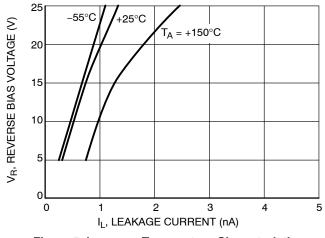


Figure 3. Typical Junction Capacitance vs Reverse Voltage

Figure 4. V_{BR} versus I_T Characteristics



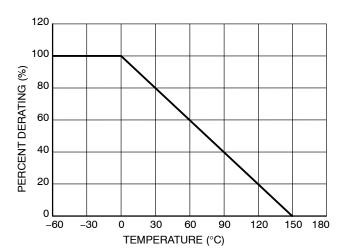


Figure 5. I_R versus Temperature Characteristics

Figure 6. Temperature Power Dissipation Derating

APPLICATIONS

Surge protection diodes provide a low cost solution to conducted and radiated Electromagnetic Interference (EMI) and Electrostatic Discharge (ESD) noise problems. The noise immunity level and reliability of FlexRay transceivers can be easily increased by adding external surge protection diodes to prevent transient voltage failures.

The NUP2115L provides a surge protection solution for FlexRay data communication lines. The NUP2115L is a dual bidirectional surge protection device in a compact SOT–23 package. This device is based on Zener technology that optimizes the active area of a PN junction to provide robust protection against transient EMI surge voltage and ESD.

Surge Protection Diode Protection Circuit

Surge protection diodes provide protection to a transceiver by clamping a surge voltage to a safe level. surge protection diodes have high impedance below and low impedance above their breakdown voltage. A surge protection Zener diode has its junction optimized to absorb the high peak energy of a transient event, while a standard Zener diode is designed and specified to clamp a steady state voltage.

Figure 7 provides an example of a dual bidirectional surge protection diode array that can be used for protection with the FlexRay network. The bidirectional array is created from four identical Zener surge protection diodes. The clamping voltage of the composite device is equal to the breakdown voltage of the diode that is reversed biased, plus the diode drop of the second diode that is forwarded biased.

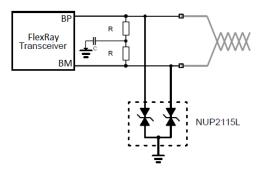


Figure 7. FlexRay Surge Protection Circuit

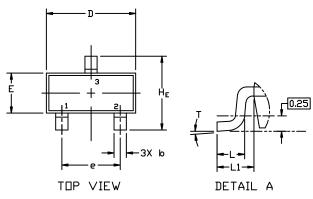


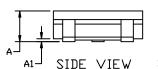


SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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